

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Amend the paragraph beginning on page 17, line 16 as follows:

As shown in Fig. 7B, the silicon substrate ~~110~~ 100 is heated to a temperature of 330 °C to 395 °C, more preferably to a temperature of 345 °C to 390 °C, e.g., to 355 °C, and Co is deposited by sputtering. The deposited Co layer 111 is partially mixed with Si on the silicon layer to form a Co-Si composite layer 112. A TiN layer 114 is deposited on the Co layer 111 at a substrate temperature of 150 °C to a thickness of 30 nm for example.